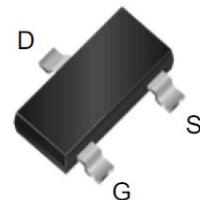


WPM2081

Single P-Channel, -20V, -4A, Power MOSFET

[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

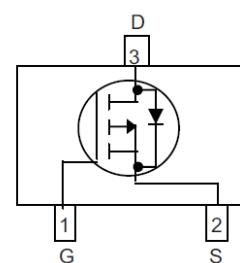
V_{DS} (V)	Typical R_{DS(on)} (mΩ)
-20	41 @ V _{GS} =-4.5V
	55 @ V _{GS} =-2.5V



SOT-23

Descriptions

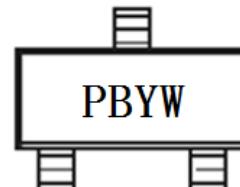
The WPM2081 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WPM2081 is Pb-free.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance
- Extremely Low Threshold Voltage
- Small package SOT-23



PB = Device Code
Y = Year
W = Week(A~z)

Applications

- DC/DC converters
- Power supply converters circuit
- Load/Power Switching for portable device

Marking

Order information

Device	Package	Shipping
WPM2081-3/TR	SOT-23	3000/Tape&Reel

Absolute Maximum ratings

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	-20		V
Gate-Source Voltage	V _{GS}	±12		
Continuous Drain Current ^a	I _D	-4	-3.5	A
		-3.2	-2.8	
Maximum Power Dissipation ^b	P _D	0.96	0.80	W
		0.62	0.52	
Pulsed Drain Current ^c	I _{DM}	-12		A
Operating Junction Temperature	T _J	-55 to 150		°C
Lead Temperature	T _L	260		°C
Storage Temperature Range	T _{stg}	-55 to 150		°C

Thermal resistance ratings

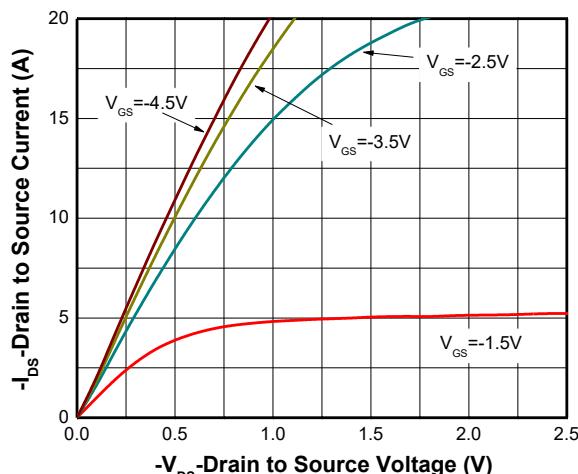
Single Operation					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient Thermal Resistance ^a	t ≤ 10 s	R _{θJA}	79	99	°C/W
	Steady State		104	130	
Junction-to-Case Thermal Resistance	R _{θJC}	40	60		

- a. The value of R_{θJA} is measured with the device mounted on 1-inch² (6.45cm²) with 2oz.(0.071mm thick) Copper pad on a 1.5*1.5 inch², 0.06-inch thick FR4 PCB, in a still air environment with T_A =25°C. The value in any given application is determined by the user's specific board design
- b. The power dissipation P_D is based on Junction-to-Ambient thermal resistance R_{θJA} t ≤ 10s value and the T_{J(MAX)}=150°C.
- c. Repetitive rating, ~10us pulse width, duty cycle ~1%, keep initial T_J =25°C, the maximum allowed junction temperature of 150°C.
- d. The static characteristics are obtained using ~380us pulses, duty cycle ~1%.

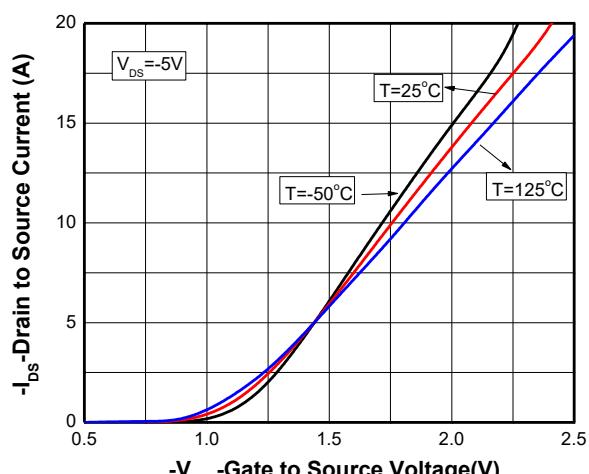
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0 \text{ V}, I_D = -250\mu\text{A}$	-20			V
Zero Gate Voltage Drain Current	I_{DS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.35	-0.65	-1	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -3.2 \text{ A}$		41	52	$\text{m}\Omega$
		$V_{GS} = -2.5 \text{ V}, I_D = -3.0 \text{ A}$		55	81	
		$V_{GS} = -1.8 \text{ V}, I_D = -2.5 \text{ A}$		72	110	
Forward Transconductance	g_{FS}	$V_{DS} = -5 \text{ V}, I_D = -4 \text{ A}$		6	16	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}, V_{DS} = -6 \text{ V}$		1062		pF
Output Capacitance	C_{oss}			146		
Reverse Transfer Capacitance	C_{rss}			124		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V}, I_D = -3.3 \text{ A}$		10		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.8		
Gate-to-Source Charge	Q_{GS}			1.8		
Gate-to-Drain Charge	Q_{GD}			1.7		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5 \text{ V}, V_{DS} = -6 \text{ V}, I_D = -3.3 \text{ A}, R_G = 6\Omega$		11.4		ns
Rise Time	t_r			6.8		
Turn-Off Delay Time	$t_{d(OFF)}$			67.6		
Fall Time	t_f			16.8		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = -3.2 \text{ A}$		-0.8	-1.5	V

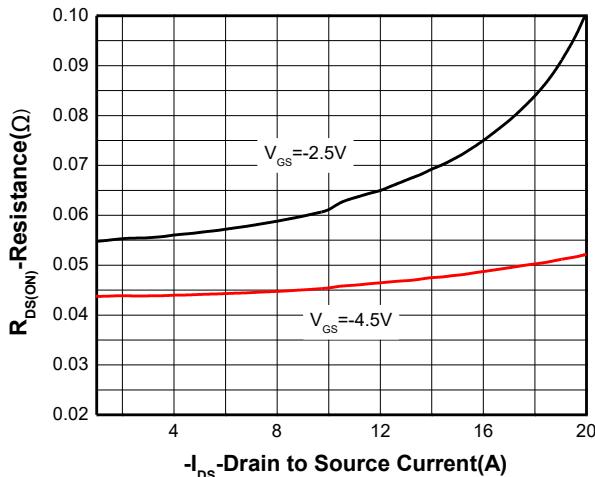
Typical Characteristics (Ta=25°C, unless otherwise noted)



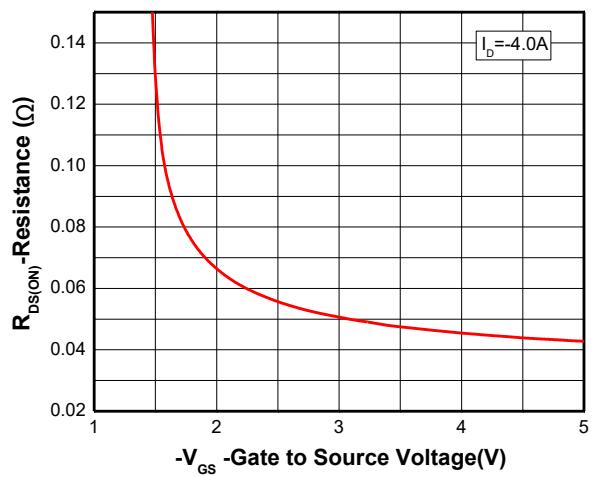
Output characteristics



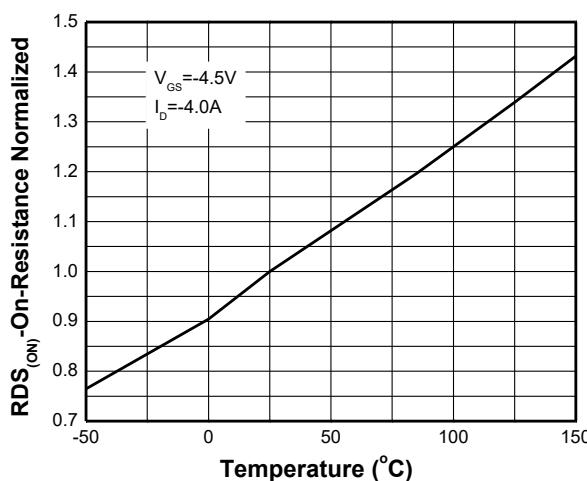
Transfer characteristics



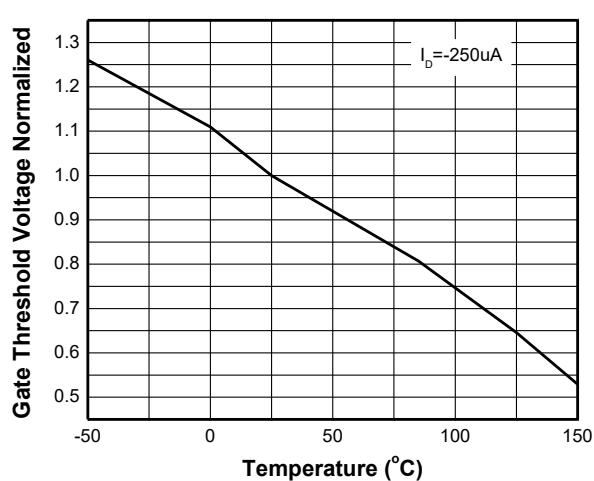
On-Resistance vs. Drain current



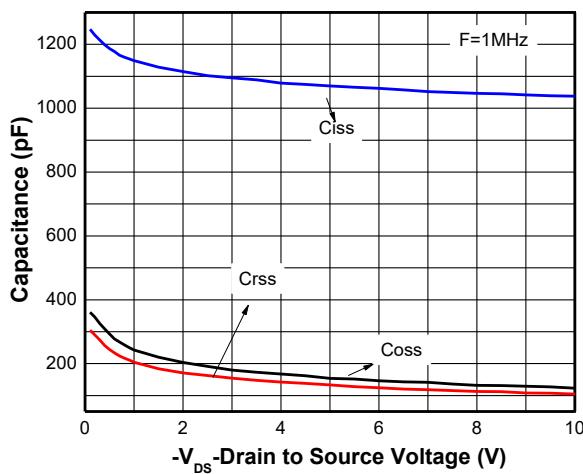
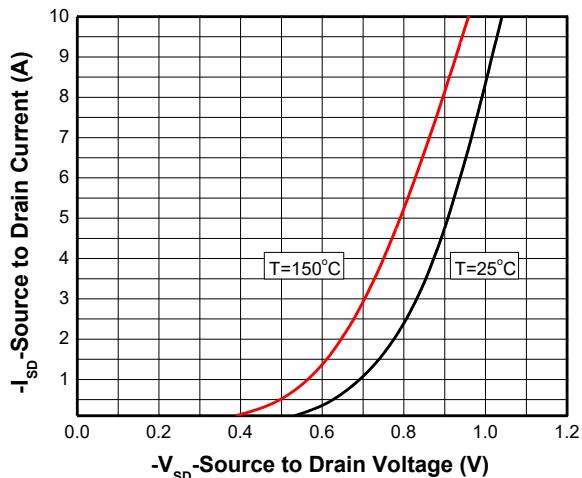
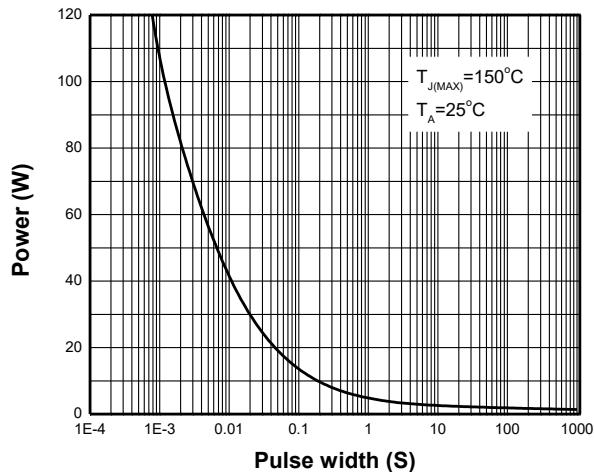
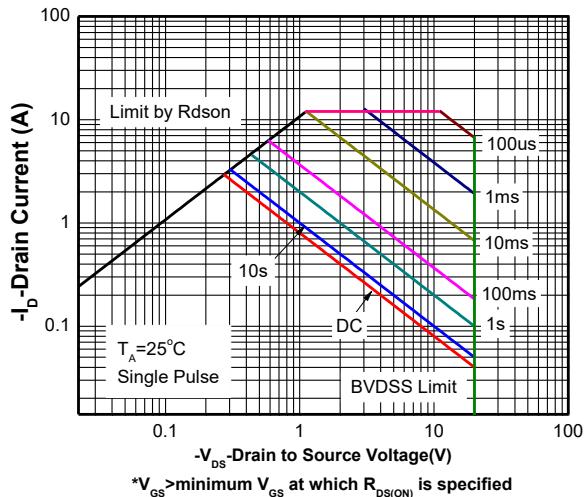
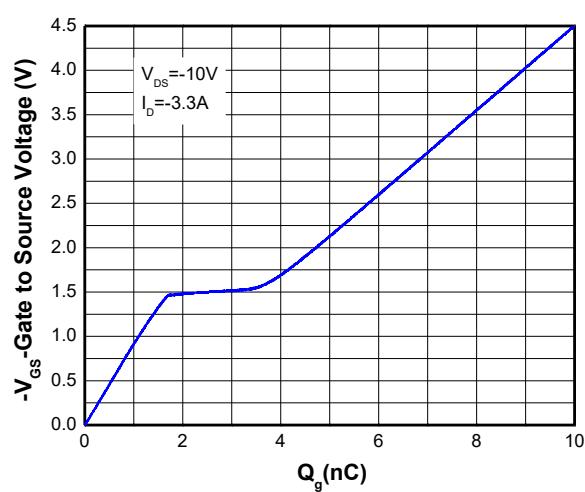
On-Resistance vs. Gate-to-source voltage

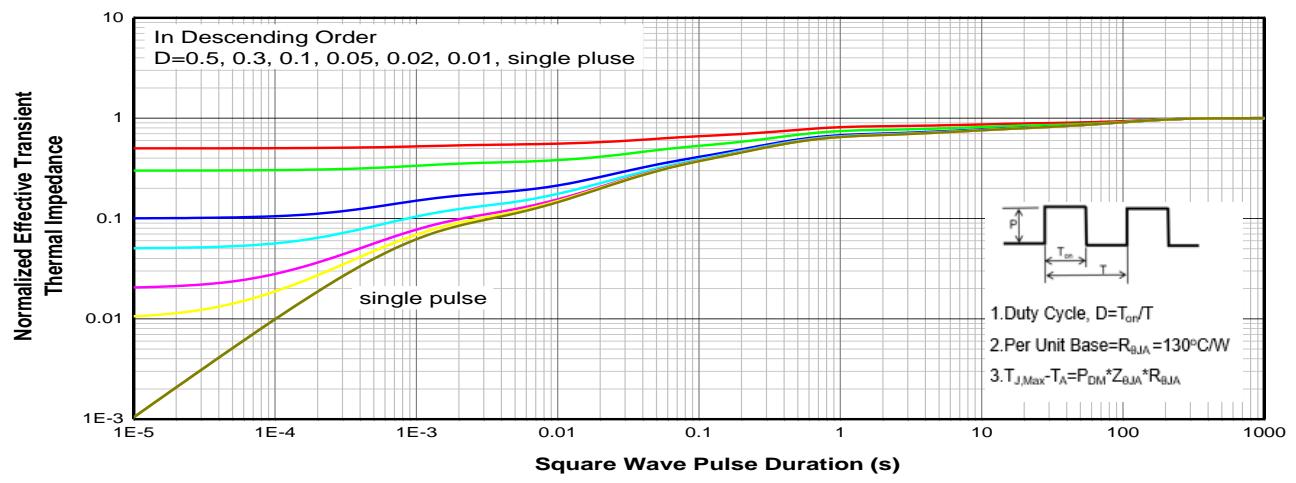


On-Resistance vs. Junction temperature



Threshold voltage vs. Temperature

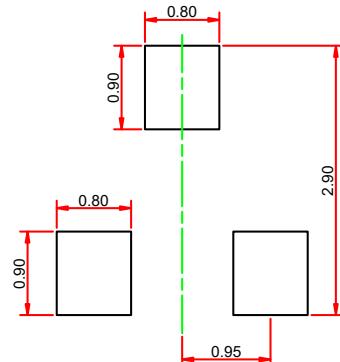
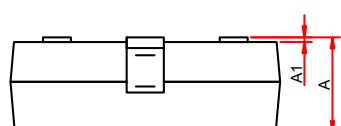
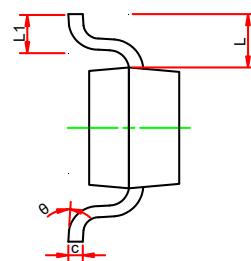
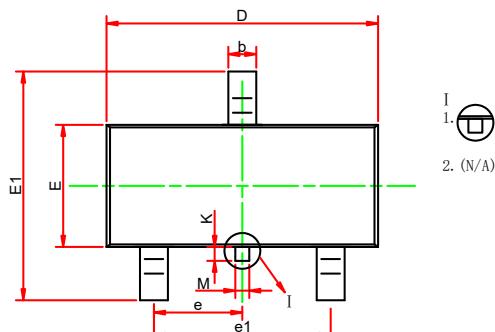

Capacitance

Body diode forward voltage

Single pulse power

Safe operating power

Gate Charge Characteristics



Transient Thermal Response (Junction-to-Ambient)

PACKAGE OUTLINE DIMENSIONS

SOT-23

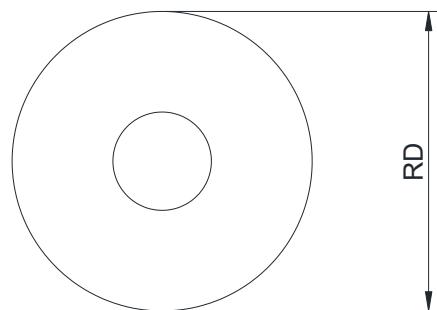


RECOMMENDED LAND PATTERN(unit:mm)

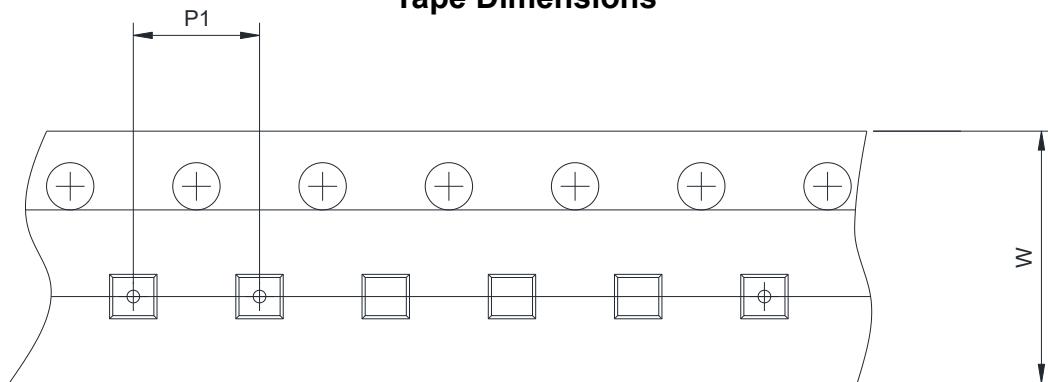
Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.89	1.10	1.30
A1	0.00	-	0.10
b	0.30	0.43	0.55
c	0.05	-	0.20
D	2.70	2.90	3.10
E	1.15	1.33	1.50
E1	2.10	2.40	2.70
e	0.95 Typ.		
e1	1.70	1.90	2.10
L	0.45	0.55	0.65
L1	0.20	0.35	0.60
M	0.10	0.15	0.25
K	0.00	-	0.25
θ	0 °	-	8 °

TAPE AND REEL INFORMATION

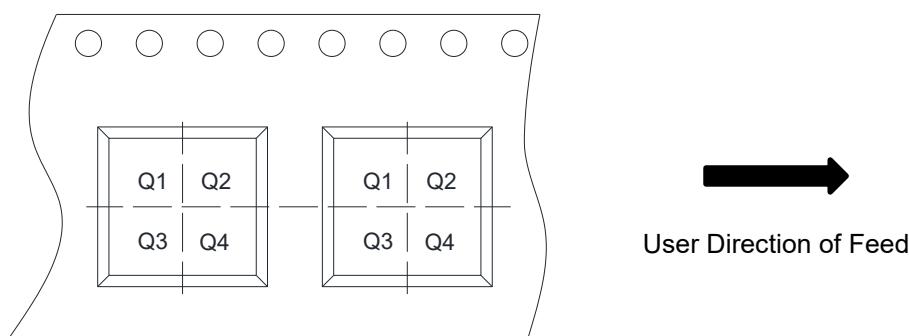
Reel Dimensions



Tape Dimensions



Quadrant Assignments For PIN1 Orientation In Tape



RD	Reel Dimension	<input checked="" type="checkbox"/> 7inch <input type="checkbox"/> 13inch
W	Overall width of the carrier tape	<input checked="" type="checkbox"/> 8mm <input type="checkbox"/> 12mm <input type="checkbox"/> 16mm
P1	Pitch between successive cavity centers	<input type="checkbox"/> 2mm <input checked="" type="checkbox"/> 4mm <input type="checkbox"/> 8mm
Pin1	Pin1 Quadrant	<input type="checkbox"/> Q1 <input type="checkbox"/> Q2 <input checked="" type="checkbox"/> Q3 <input type="checkbox"/> Q4